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Kind regards,

Team Nexperia

0.2 A very low V<sub>F</sub> MEGA Schottky barrier rectifiers

Rev. 01 — 24 November 2006

Produ

**Product data sheet** 

### **Product profile**

### 1.1 General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifiers with an integrated guard ring for stress protection, encapsulated in ultra small and flat lead Surface-Mounted Device (SMD) plastic packages.

Table 1. **Product overview** 

Type number	Package		Configuration
	NXP	JEITA	
PMEG6002EB	SOD523	SC-79	single
PMEG6002TV	SOT666	-	dual isolated

### 1.2 Features

Forward current: I<sub>F</sub> ≤ 0.2 A

Reverse voltage: V<sub>R</sub> ≤ 60 V

Very low forward voltage

Ultra small and flat lead SMD plastic packages

### 1.3 Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch mode power supply
- Reverse polarity protection
- Low power consumption applications

#### 1.4 Quick reference data

Table 2. **Quick reference data** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per diode						
l <sub>F</sub>	forward current	T <sub>amb</sub> ≤ 25 °C	-	-	0.2	Α
$V_R$	reverse voltage		-	-	60	V
$V_{F}$	forward voltage	$I_F = 200 \text{ mA}$	[1] _	540	600	mV

[1] Pulse test:  $t_p \le 300 \ \mu s$ ;  $\delta \le 0.02$ .



## 2. Pinning information

Table 3. Pinning

Table 3.	Pinning		
Pin	Description	Simplified outline	Symbol
SOD523			
1	cathode	[1]	
2	anode	1 2	1 <del>    2</del> sym001
SOT666	onedo (diedo 4)		<u>,                                      </u>
1	anode (diode 1)	6 5 4	6 5 4
2	not connected		
3	cathode (diode 2)		
4	anode (diode 2)		
5	not connected	1 2 3	1 2 3 <i>006aaa440</i>
6	cathode (diode 1)	1 2 3	

<sup>[1]</sup> The marking bar indicates the cathode.

# 3. Ordering information

Table 4. Ordering information

Type number	Package					
	Name	Description	Version			
PMEG6002EB	SC-79	plastic surface-mounted package; 2 leads	SOD523			
PMEG6002TV	-	plastic surface-mounted package; 6 leads	SOT666			

## 4. Marking

Table 5. Marking codes

Type number	Marking code
PMEG6002EB	B2
PMEG6002TV	1B

## 5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per diode					
$V_R$	reverse voltage		-	60	V
l <sub>F</sub>	forward current	$T_{amb} \le 25  ^{\circ}C$	-	0.2	Α
I <sub>FRM</sub>	repetitive peak forward current	$\begin{array}{l} t_p \leq 1 \text{ ms;} \\ \delta \leq 0.25 \end{array}$	-	2	Α
I <sub>FSM</sub>	non-repetitive peak forward current	square wave; t <sub>p</sub> = 8 ms	<u>[1]</u> -	2.5	А
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C			
	PMEG6002EB		<u>[1]</u> _	300	mW
	PMEG6002TV		<u>[1]</u> _	200	mW
			[2] _	300	mW
Per devic	е				
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25  ^{\circ}C$			
	PMEG6002TV		<u>[1]</u> _	300	mW
			[2] _	400	mW
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		-65	+150	°C
T <sub>stg</sub>	storage temperature		-65	+150	°C

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

<sup>[2]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm<sup>2</sup>.

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### 6. Thermal characteristics

Table 7 Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per device							
· -ui(j-a)	thermal resistance from junction to ambient	in free air					
	PMEG6002EB		[1][2]	-	-	400	K/W
	PMEG6002TV		[1][2]	-	-	416	K/W
			[1][3]	-	-	318	K/W
· -ti (j-sp)	thermal resistance from junction to solder point		[4]				
	PMEG6002EB			-	-	75	K/W
	PMEG6002TV			-	-	195	K/W

<sup>[1]</sup> For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P<sub>R</sub> are a significant part of the total power losses.

### 7. Characteristics

Table 8. Characteristics

 $T_{amb}$  = 25 °C unless otherwise specified.

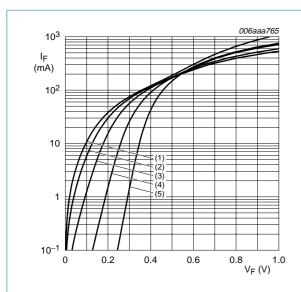
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per diod	е					
$V_{F}$	forward voltage		<u>[1]</u>			
		$I_F = 0.1 \text{ mA}$	-	130	170	mV
	$I_F = 1 \text{ mA}$	-	190	230	mV	
	$I_F = 10 \text{ mA}$	-	260	300	mV	
		$I_F = 100 \text{ mA}$	-	420	470	mV
		$I_F = 200 \text{ mA}$	-	540	600	mV
$I_R$	reverse current					
		V <sub>R</sub> = 10 V	-	2	10	μΑ
		$V_R = 60 \text{ V}$	-	20	100	μΑ
		$V_R = 10 \text{ V}; T_{amb} = 100 ^{\circ}\text{C}$	-	310	-	μΑ
$C_{d}$	diode capacitance	$V_R = 1 V$ ; $f = 1 MHz$	-	14	20	pF

<sup>[1]</sup> Pulse test:  $t_p \le 300~\mu s;~\delta \le 0.02.$ 

<sup>[2]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

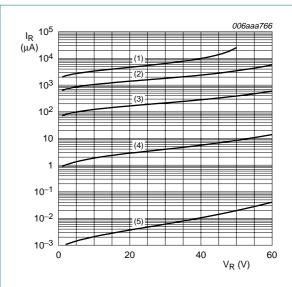
<sup>[3]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm<sup>2</sup>.

<sup>[4]</sup> Soldering point of cathode tab.



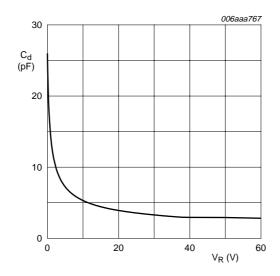
- (1)  $T_{amb} = 150 \, ^{\circ}C$
- (2)  $T_{amb} = 125 \, ^{\circ}C$
- (3)  $T_{amb} = 85 \, ^{\circ}C$
- (4)  $T_{amb} = 25 \, ^{\circ}C$
- (5)  $T_{amb} = -40 \, ^{\circ}C$

Fig 1. Forward current as a function of forward voltage; typical values



- (1)  $T_{amb} = 150 \, ^{\circ}C$
- (2)  $T_{amb} = 125 \, ^{\circ}C$
- (3)  $T_{amb} = 85 \, ^{\circ}C$
- (4)  $T_{amb} = 25 \, ^{\circ}C$
- (5)  $T_{amb} = -40 \, ^{\circ}C$

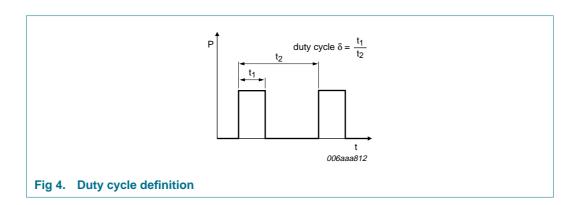
Fig 2. Reverse current as a function of reverse voltage; typical values



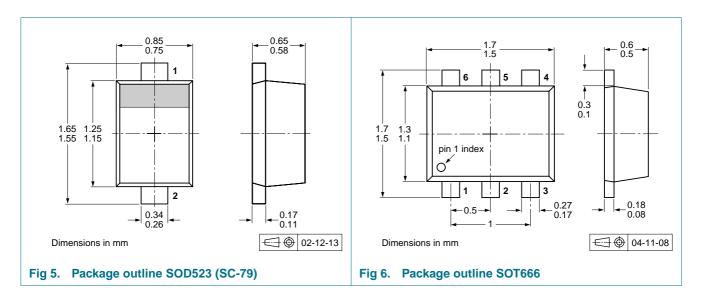
 $f = 1 \text{ MHz}; T_{amb} = 25 \,^{\circ}\text{C}$ 

Fig 3. Diode capacitance as a function of reverse voltage; typical values

### 8. Test information



### 9. Package outline



## 10. Packing information

Table 9. Packing methods

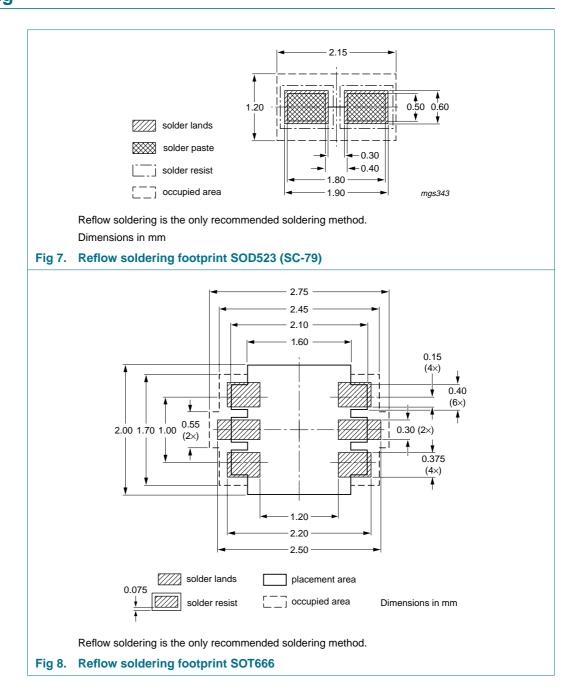
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number Package		Description	Packing quantity			
			3000	4000	8000	10000
PMEG6002EB	SOD523	2 mm pitch, 8 mm tape and reel	-	-	-315	-
	4 mm pitch, 8 mm tape and reel	-115	-	-	-135	
PMEG6002TV	SOT666	2 mm pitch, 8 mm tape and reel	-	-	-315	-
		4 mm pitch, 8 mm tape and reel	-	-115	-	-

<sup>[1]</sup> For further information and the availability of packing methods, see  $\underline{\text{Section 14}}$ .

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# 11. Soldering



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# 12. Revision history

### Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PMEG6002EB_PMEG6002TV_1	20061124	Product data sheet	-	-

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#### 13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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### **NXP Semiconductors**

# PMEG6002EB; PMEG6002TV

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